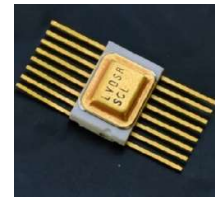


HIGH SPEED
QUAD LVDS RECEIVER
(SC1003-1)
(Radiation Tolerant)



DATA SHEET
Version 1.0, March 2019



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RT HIGH SPEED QLVDS RECEIVER (SC1003-1)

PRODUCT DESCRIPTION:

The SC1003-1 is a quad, low-voltage, differential signaling (QLVDS) line receiver specifically designed and packaged for use in aerospace environments in a low-power and fast point-to-point baseband data transmission standard.

Any of the four differential receivers provides a valid logical output state with a $\pm 100\text{mV}$ differential input voltage within the input common-mode voltage range.

The circuit features an internal fail safe function to ensure a known output state in case of an input short circuit or floating.

The intended application of these devices and signaling technique is point-to-point data transmission over controlled impedance media of approximately 100 ohm. The transmission media may be printed-circuit board traces, backplanes or cables.

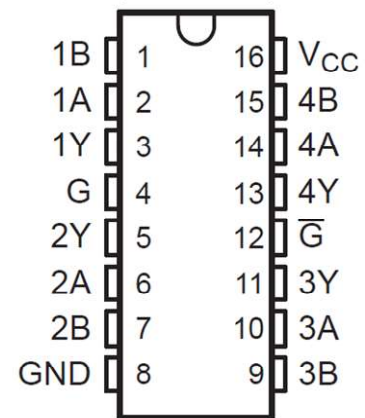
FEATURES:

- Operating Power Supply $3.3\text{V} \pm 0.3\text{V}$
- Cold Sparring at LVDS input pins
- LVDS input levels and CMOS logic output levels
- Compatible with ANSI/TIA/EIA-644 LVDS standard
- 400 Mbps (200 MHz) switching rates
- Differential input thresholds $\pm 100\text{mV}$
- Open circuit fail safe function
- Power dissipation 76 mW Typical per receiver at 200MHz ($V_{DD}=3.3\text{V}$)
- Propagation delay ≤ 5 nsec.
- Operating Temperature Range: -55°C to 125°C
- 16 Pin CSOP /Customized package /Die
- Radiation Tolerant up to 200 KRad
- SET/SEL immune up to $50 \text{ MeV.cm}^2/\text{mg}$
- Pin compatible with QLVDS receiver LVDS32
- ESD protection level: HBM class-1 ($< 1999\text{V}$)
- Latch up current protection $\pm 100\text{mA}$
- $\Theta_{JC} = 3.1^{\circ}\text{C/Watt}$
- SCL's 180nm CMOS Technology

PIN CONFIGURATION:

Pin No.	Pin Name	Description
16	V_{DD}	+3.3V Supply
8	GND	Supply Ground
4,12	G / \bar{G}	Control inputs
1,7,9,15	(1,2,3,4) B	receiver input pin (Inverting)
2,6,10,14	(1,2,3,4) A	receiver input pin (Non-inverting)
3,5,11,13	(1,2,3,4) Y	Driver o/p pin, TTL/CMOS compatible

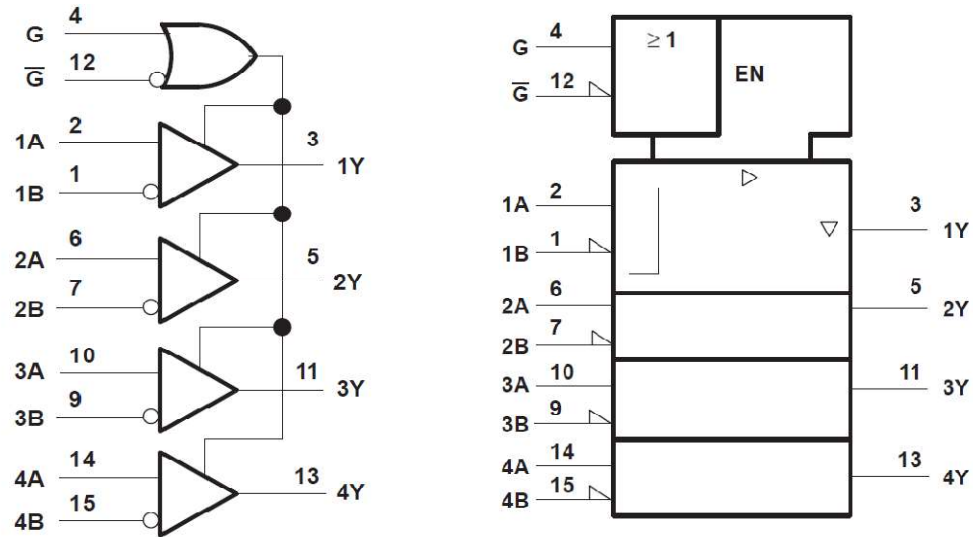
Device Pin Description



Device Pin Diagram



FUNCTIONAL DESCRIPTION:



Logic Diagram and Logic Symbol

Differential Input	Enable		Outputs
	A , B	G	
VID ≥ 100mV	H	X	H
	X	L	H
-100mV > VID > 100mV	H	X	?
	X	L	?
VID ≤ -100mV	H	X	L
	X	L	L
OPEN	H	X	H
	X	L	H
Don't care (X)	L	H	Z
L=low level, H=high level, X=irrelevant, Z=high impedance, ?=indeterminate			

Functional Truth Table



ABSOLUTE MAXIMUM RATINGS (1):

Over operating free-air temperature range (unless otherwise noted)

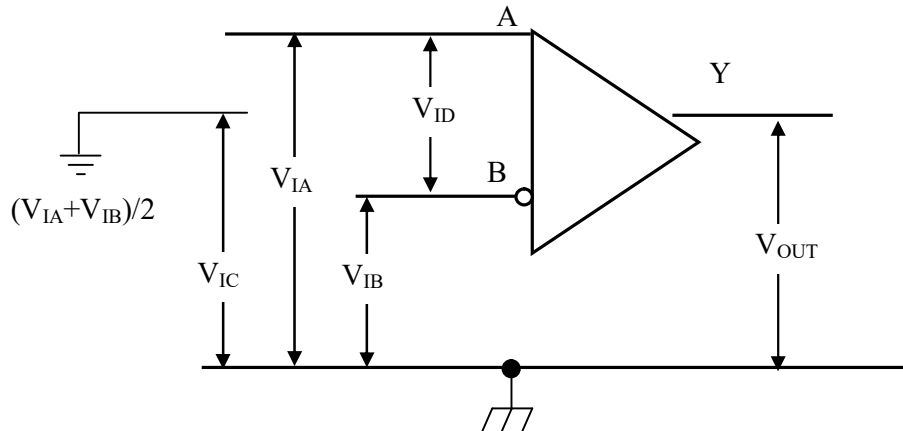
PARAMETER		UNIT
Supply Voltage Range (V_{DD})		-0.5V to 4.3V
Voltage Range (V_I)	Enables and Output	-0.5V to $V_{DD} + 0.5V$
	A or B	-0.5 V to 4.0 V
Max. Junction Temperature (T_J)		150°C
Storage Temperature Range (T_{STG})		-65°C to 150°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS:

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{DD}	Supply Voltage	3	3.3	3.6	V
V_{IH}	High Level Input Voltage (G / \bar{G})	2.0	-	-	V
V_{IL}	Low Level Input Voltage (G / \bar{G})	-	-	0.8	V
$ V_{ID} $	Magnitude Of Differential Input Voltage	0.1	-	0.6	V
V_{IC}	Common Mode Input Voltage Range	$ V_{ID} / 2$	-	$2.4 - (V_{ID} / 2)$	V
T_A	Operating Free Air Temperature	-55	-	+125	°C

TEST CIRCUIT:





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DC ELECTRICAL SPECIFICATIONS:

Test condition: $V_{DD} = 3.3V \pm 0.3V$, $T_{AMB} = -55^{\circ}C$ to $125^{\circ}C$

Symbol	Parameters	Test Conditions	Pin	Min.	Typ.	Max.	Units
V_{ITH+}	Input Voltage High	$V_{IC} = 1.2V$	A, B	-	-	100	mV
V_{ITH-}	Input Voltage Low	$V_{IC} = 1.2V$		-100	-	-	mV
V_{OH}	Output Voltage High	$I_{OH} = -8mA$	Y	2.4	3.1	-	V
V_{OL}	Output Voltage Low	$I_{OL} = +8mA$		-	0.13	0.4	V
I_{IH}	High Level Input Current	$V_{IH} = 2.0V$	G, \bar{G}	-	-	± 20	μA
I_{IL}	Low Level Input Current	$V_{IL} = 0.8V$		-	-	± 20	μA
I_{IN}	Receiver Input Current	$V_{IN} = 0$ or $2.4V$	A, B	-	-8.5	± 20	μA
I_{OZ}	High-impedance output current	$V_O = 0$ or V_{DD}	Y	-	-	± 10	μA
$I_{I(OFF)}$	Power-off Input Current (Cold Spare Leakage)	$V_{DD} = 0V$, $V_I = 0$ or V_{DD}	A, B	-	8.0	± 20	μA
I_{DD} (static)	I_{DDNL} (Driver Enabled)	No Load, Inputs = open/steady state	V_{DD}	15	30.0	50	mA
	I_{DDZ} (Driver Disabled)	No Load, Inputs = open/steady state		0.2	0.75	3.3	mA

AC ELECTRICAL SPECIFICATIONS:

Test condition: $V_{DD} = 3.3V$, Freq. @ 1 MHz, $C_L = 10pF$, $T_{AMB} = -55^{\circ}C$ to $125^{\circ}C$

Symbol	Parameter	Min.	Typical	Max.	Units
t_r	Output signal rise time (20% to 80%)	-	0.738	1.5	ns
t_f	Output signal fall time (20% to 80%)	-	0.568	1.5	ns
t_{PHLD}	propagation delay	1.0	2.82	5	ns
t_{PLHD}	propagation delay	1.0	2.86	5	ns
$T_{SKD} = t_{PHLD} - t_{PLHD} $	skew in delay	-	0.05	0.5	ns
t_{PHZ}	Delay, high-level-to-high-impedance output	-	4.5	15	ns
t_{PLZ}	Delay, low-level-to-high-impedance output	-	4.8	15	ns
t_{PZH}	Delay, high-impedance-to-high-level output	-	4.4	15	ns
$*t_{PZL}$	Delay, high-impedance-to-low-level output	-	1.6	-	us

*High Value Of t_{PZL} observed at receiver output due To high Voltage Spike at output



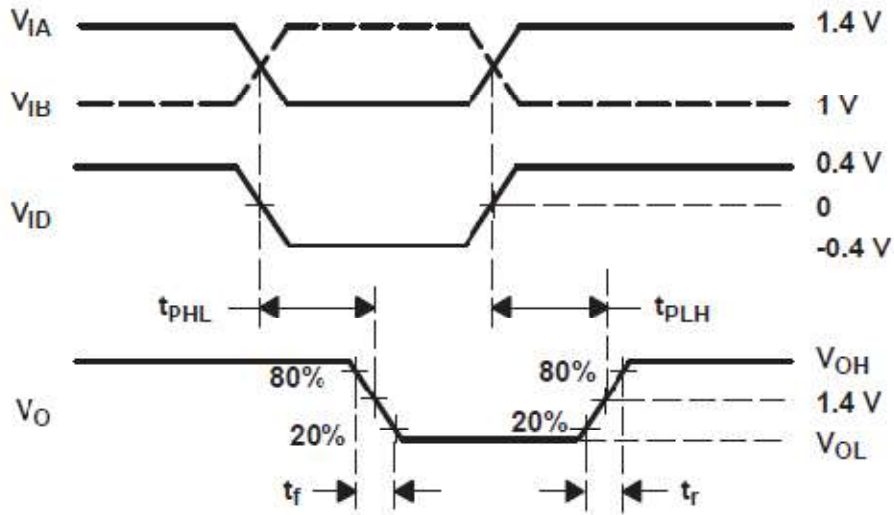
RECEIVER THRESHOLD TEST VOLTAGES:

Applied Input Voltages		Resulting Differential Input Voltages	Resulting Common Mode Input Voltages	Expected Output Voltage
V_{IA} (V)	V_{IB} (V)	V_{ID} (mV)	V_{IC} (V)	V_{OY} (V)
1.25	1.15	+100	1.20	V_{DD}
1.15	1.25	-100	1.20	V_{SS}
2.40	2.30	+100	2.35	V_{DD}
2.30	2.40	-100	2.35	V_{SS}
0.10	0.00	+100	0.05	V_{DD}
0.00	0.10	-100	0.05	V_{SS}
1.5	0.9	+600	1.20	V_{DD}
0.9	1.5	-600	1.20	V_{SS}
2.4	1.8	+600	2.10	V_{DD}
1.8	2.4	-600	2.10	V_{SS}
0.6	0.0	+600	0.30	V_{DD}
0.0	0.6	-600	0.30	V_{SS}

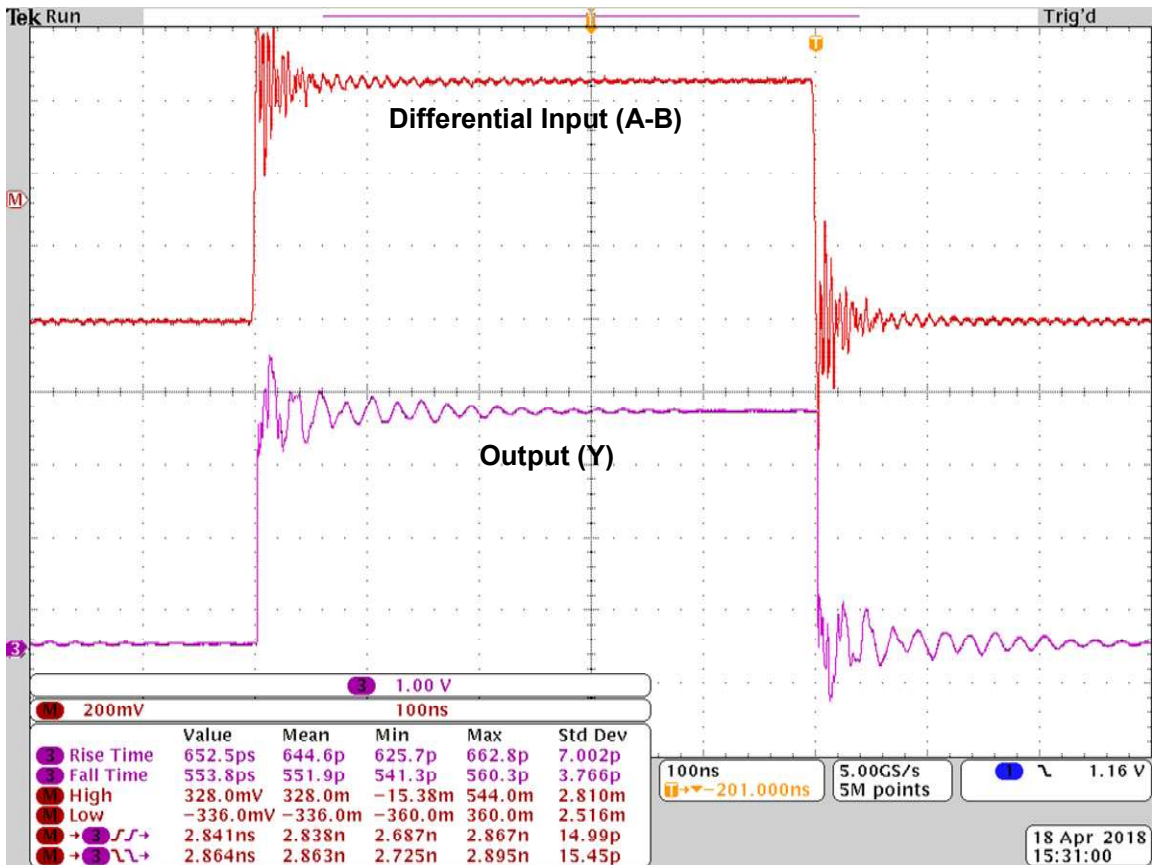
Receiver Minimum and Maximum Input Threshold Test Voltages



SWITCHING WAVEFORM:

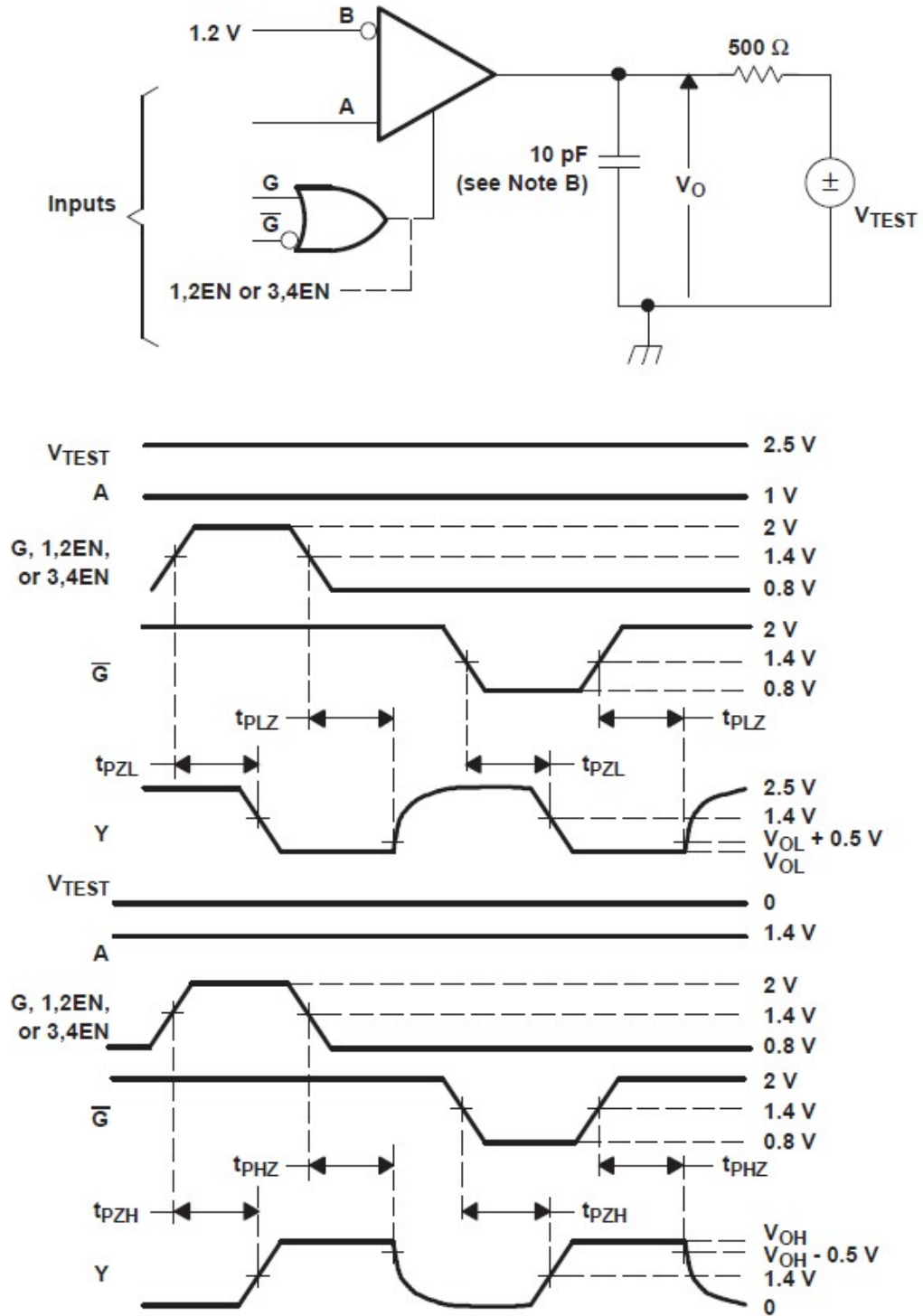


Switching Waveforms



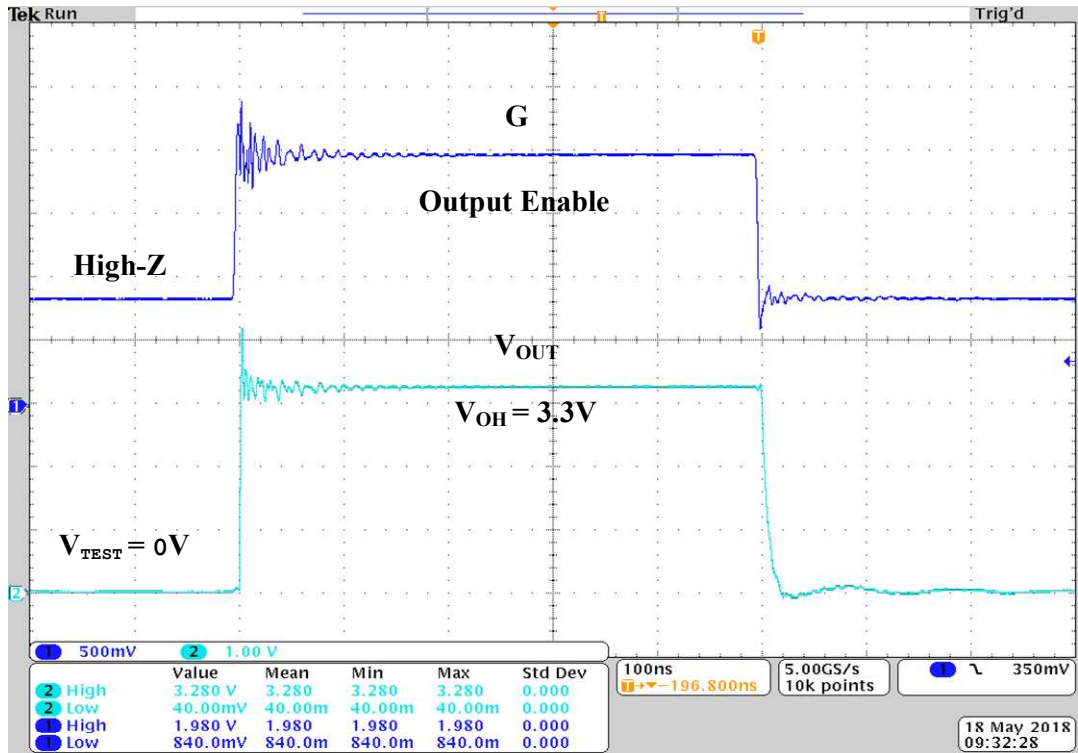


Test Circuits for High Impedance Switching Parameter Measurement

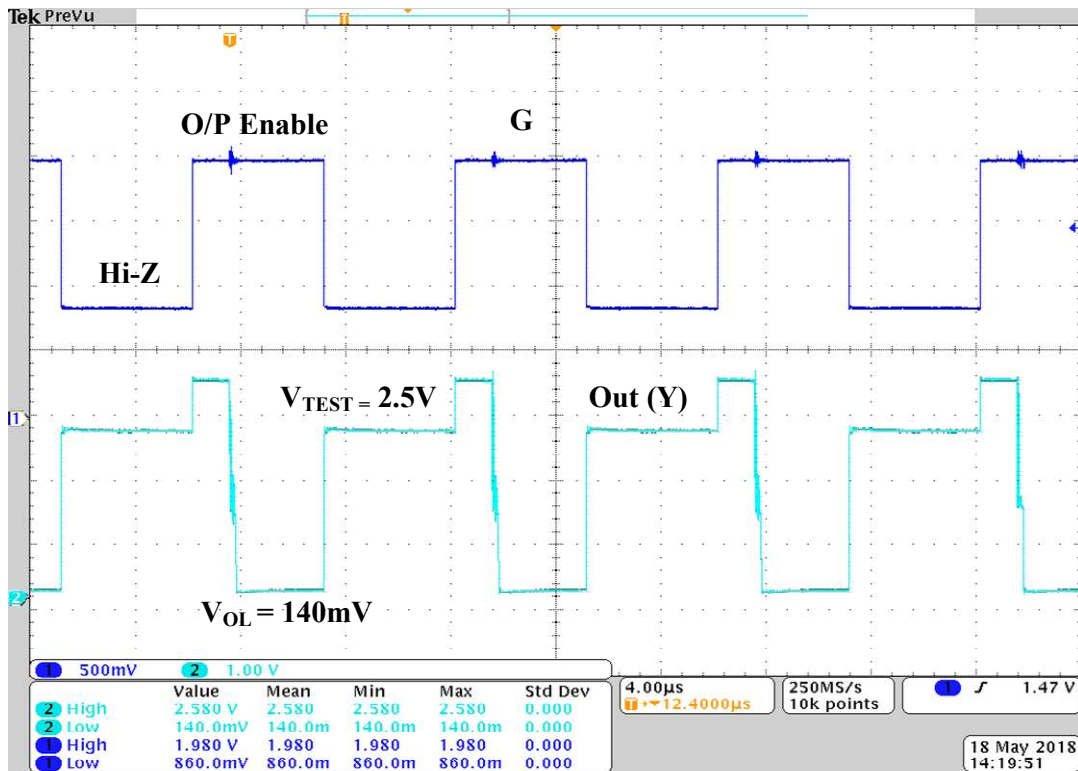




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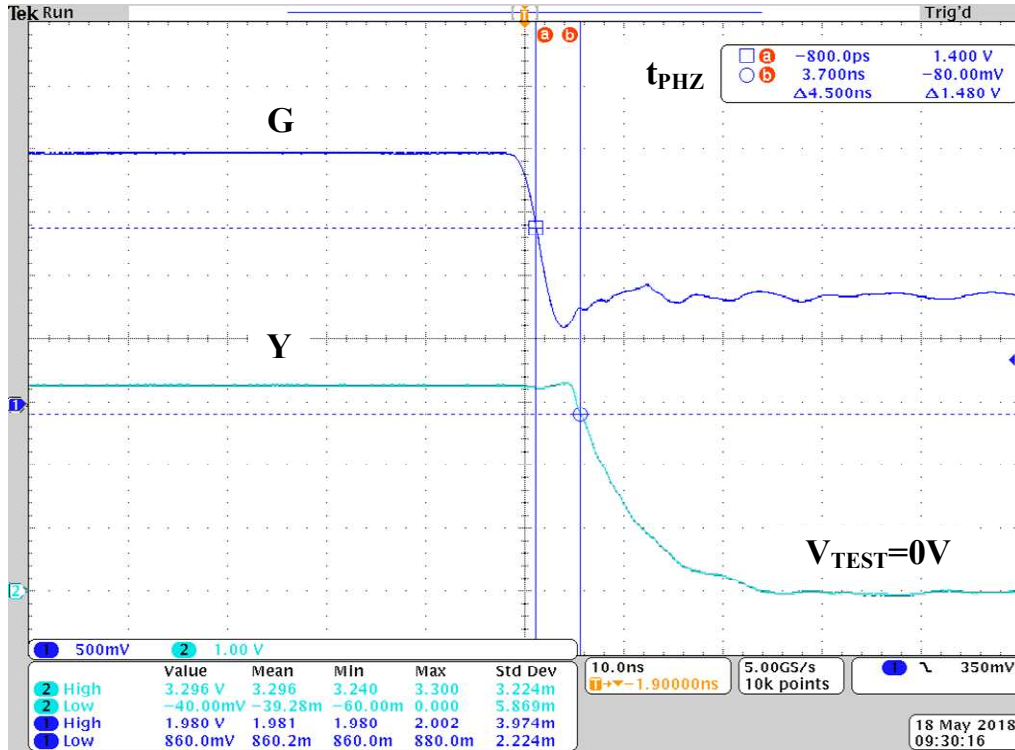
High-Z to H delay Test waveform ($V_{test}=0V$)



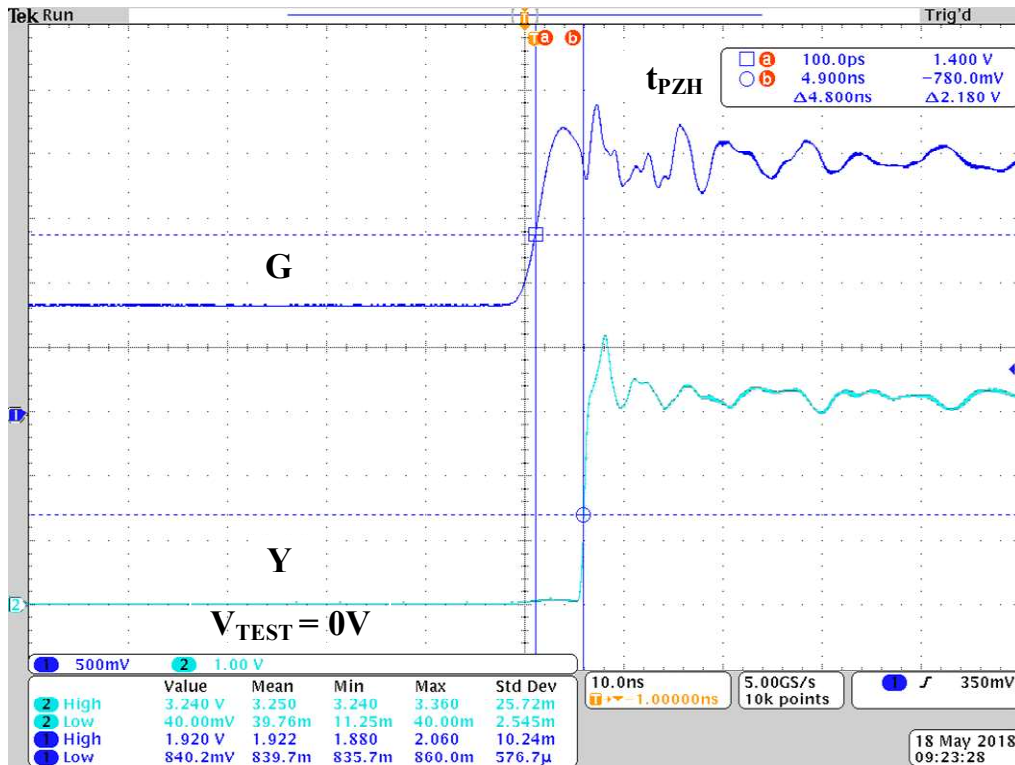
High-Z to L delay Test waveform ($V_{test}=2.5V$)



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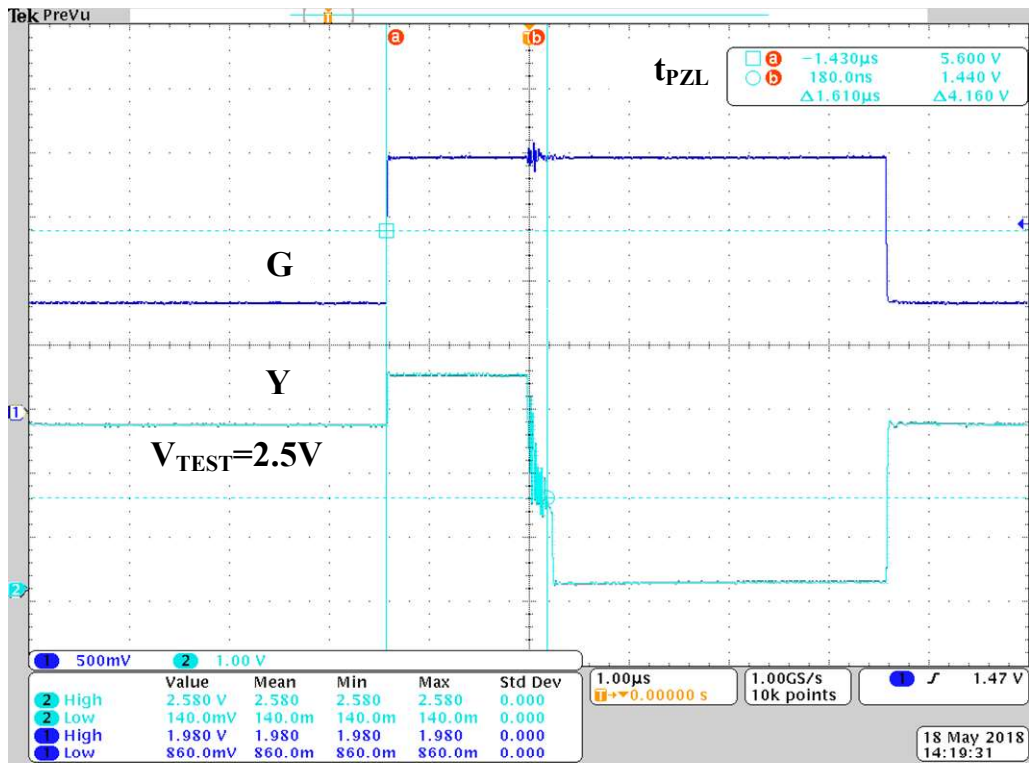
Test waveform for t_{PHZ}



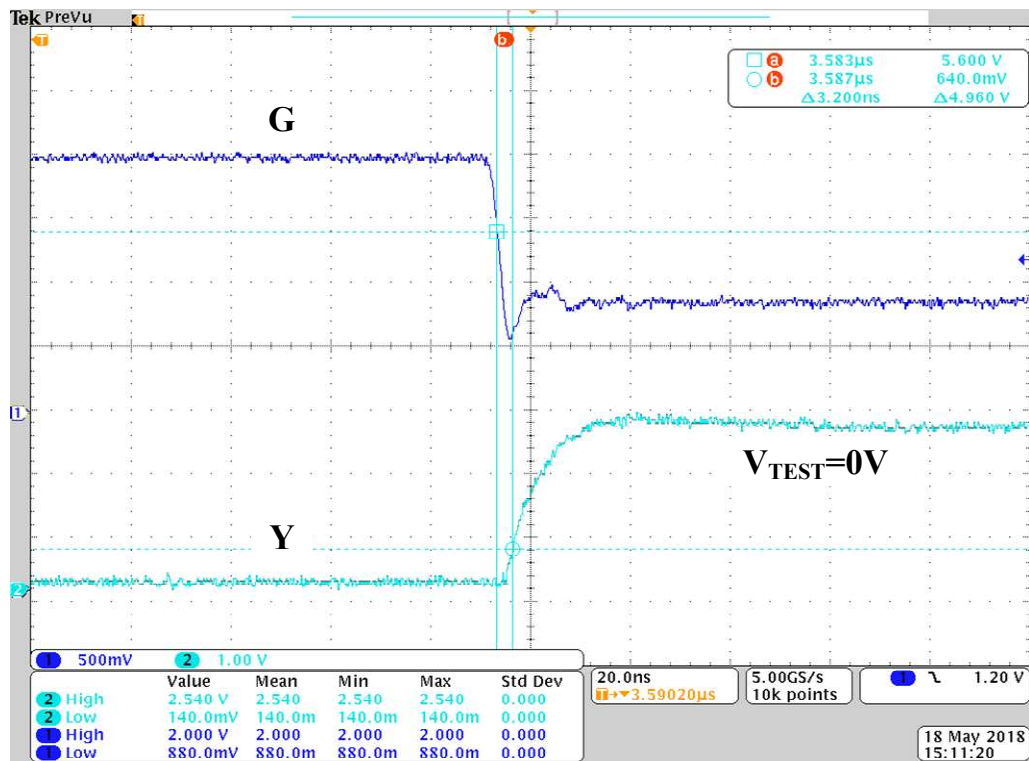
Test waveform for t_{PZH}



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Test Waveform for t_{pZL}

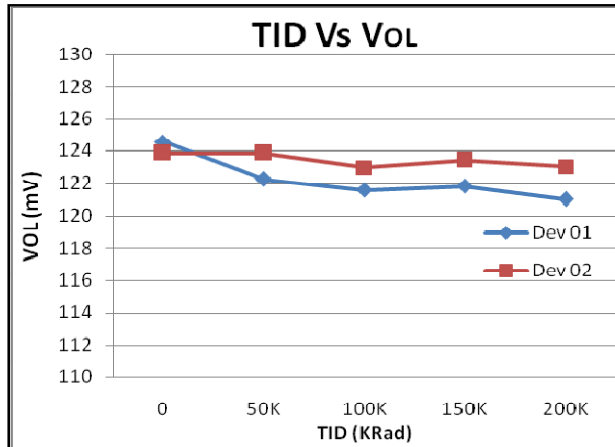
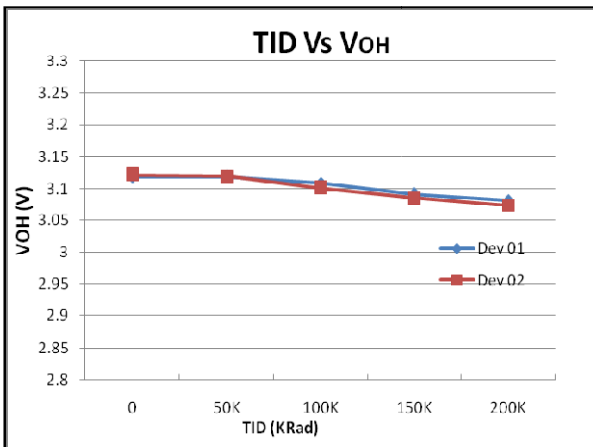
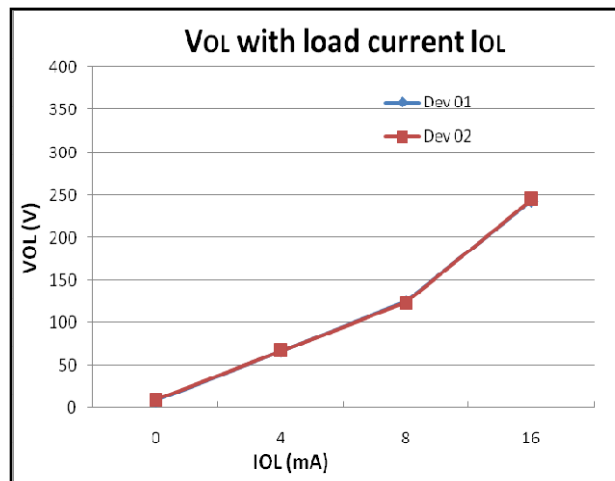
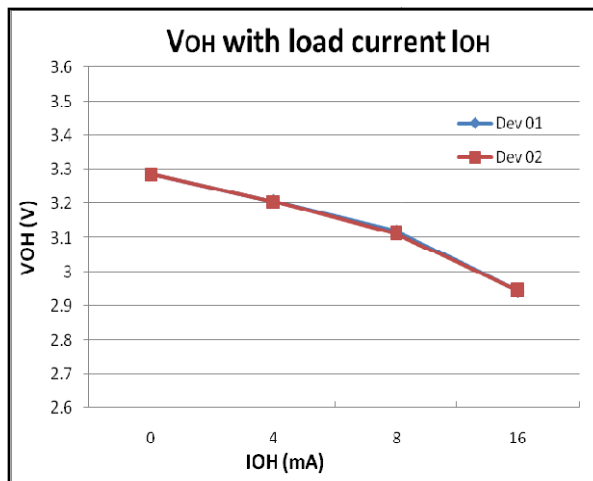
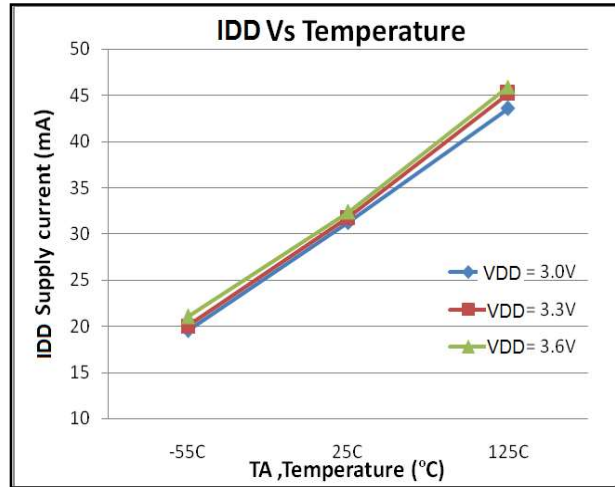
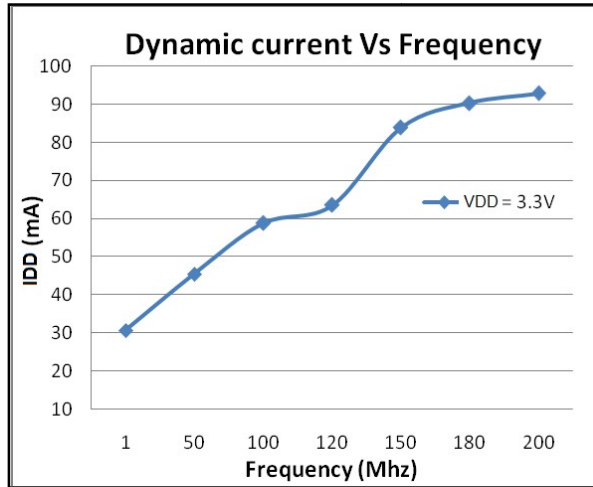


Test waveform for t_{pLZ}



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TYPICAL CHARACTERISTICS:

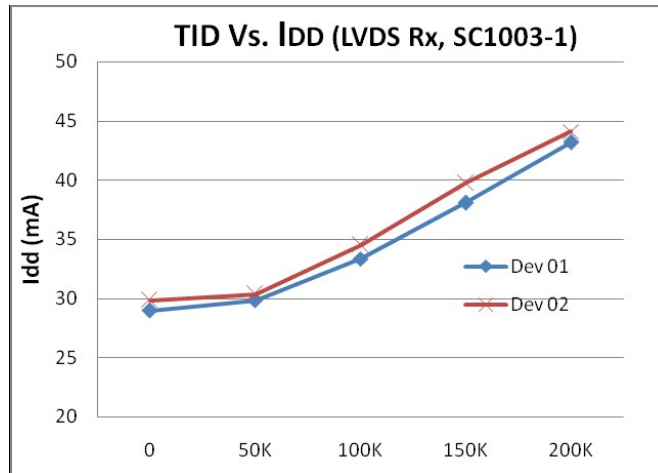




RADIATION CHARACTERISTICS:

❖ **Total Ionization Dose (TID) Testing**

- TID testing of QLVDS Receiver (SC1003-1) is performed for radiation level up to 200 KRad.
- No functional degradation and no significant change in device parameters such as IIL, IIH, VOL & VOH was observed up to 200KRad.
- Static supply current increases with radiation dose, shown in figure below.



❖ **Single Event Effect (SEE) Testing**

SEE testing of QLVDS Receiver (SC1003-1) is performed at two different LET energy ion beams Ni+ (30 MeV-cm²/mg) and Ag+ (50 MeV-cm²/mg) for a Fluence of 10⁶ ions/cm².

- No Single Event latch-up (SEL) was observed up to LET of 50 MeV-cm²/mg. Supply current (I_{DD}) remains within specification throughout testing.
- No Single Event transient (SET) was observed up to LET of 50 MeV-cm²/mg.

APPLICATION CIRCUIT:

